What Is Claimed Is:

1. A gate for preventing dopants from penetrating a gate insulator, comprising:

a gate insulator disposed on a substrate;

a polysilicon layer disposed on the gate insulator; and

an amorphous-silicon layer disposed on the polysilicon layer, wherein the gate is composed of the polysilicon layer and the amorphous-silicon layer.

2. The gate as claimed in claim 1, wherein the gate insulator is a gate oxide layer.

3. The gate as claimed in claim 1, wherein the thickness of the polysilicon layer is 300~1000Å.

4. The gate as claimed in claim 3, wherein the thickness of the amorphous-silicon layer is 1000~2000Å.

5. A method of forming a gate for preventing dopants from penetrating a gate insulator, comprising:

providing a substrate;

forming a gate insulator on the substrate;

forming a polysilicon layer on the gate insulator;

forming an amorphous-silicon layer on the polysilicon layer; and

patterning the polysilicon layer and the amorphous-silicon layer to form a gate.

6. The method as claimed in claim 5, wherein the gate insulator is a gate oxide layer.

7. The method as claimed in claim 5, wherein the thickness of the polysilicon layer is 300~1000Å.

8. The method as claimed in claim 7, wherein the method of forming the polysilicon layer comprises using silane as a processing gas to deposit the polysilicon layer under 0.15~0.25 torr at 580~630°C.

9. The method as claimed in claim 5, wherein the thickness of the amorphous-silicon layer is 1000~2000Å.

10. The method as claimed in claim 9, wherein the method of forming the amorphous-silicon layer comprises using silane as a processing gas to deposit the amorphous-silicon layer under 0.15~0.25 torr at 510~560°C.

11. The method as claimed in claim 5, wherein after the step of patterning the polysilicon layer and the amorphous-silicon layer to form the gate, a source/drain is formed in the substrate beside the gate by ion implantation.

12. The method as claimed in claim 11, wherein after performing the ion implanting, an anneal process is performed.

13. The method as claimed in claim 11, wherein a dopant used in the ion implanting process is boron ions.

14. The method as claimed in claim 13, wherein in the implantation of boron ions, the dosage is 1×10^{15}~1×10^{16} cm^{-2} and the implant energy is 3~20 keV.

15. The method as claimed in claim 11, wherein a dopant used in the ion implanting process is As ions.

16. The method as claimed in claim 15, wherein in the implantation of As ions, the dosage is 1×10^{15}~1×10^{16} cm^{-2} and the implant energy is 30~80 keV.